

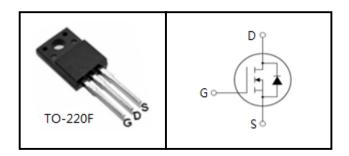
600V N-Channel MOSFET

FEATURES

- Fast switching
- Integrate fast recovery diode
- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Motor Controls
- Power Factor Correction (PFC)



| Device Marking and Package Information | | | |
|--|------------|------------|--|
| Device | ce Package | | |
| CSFR20N60F | TO-220F | CSFR20N60F | |

| Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted | | | | | | |
|--|-----------------------------------|----------|------|--|--|--|
| Devenester | Symbol | Value | | | | |
| Parameter | | TO-220F | Unit | | | |
| Drain-Source Voltage ($V_{GS} = 0V$) | V _{DSS} | 600 | V | | | |
| Continuous Drain Current | I _D | 20 | А | | | |
| Pulsed Drain Current (note1) | I _{DM} | 80 | А | | | |
| Gate-Source Voltage | V _{GSS} | ±30 | V | | | |
| Single Pulse Avalanche Energy (note2) | E _{AS} | 1201.3 | mJ | | | |
| Avalanche Current (note1) | I _{AS} | 15.5 | А | | | |
| Repetitive Avalanche Energy (note1) | E _{AR} | 720.8 | mJ | | | |
| Power Dissipation ($T_c = 25^{\circ}C$) | P _D | 120 | W | | | |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | -55~+150 | ٥C | | | |

| Thermal Resistance | | | | |
|---|-------------------|---------|-----------|--|
| Peremeter | Symbol | Value | L lus i é | |
| Parameter | Symbol | TO-220F | Unit | |
| Thermal Resistance, Junction-to-Case | R _{thJC} | 1.04 | 00.00/ | |
| Thermal Resistance, Junction-to-Ambient | R _{thJA} | 62.5 | - °C/W | |



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| Specifications $T_J = 25^{\circ}C$, unless otherwise noted | | | | | | | | |
|--|----------------------|---|-------|------|------|------|--|--|
| Parameter | Ourseland | Test Osnelitions | Value | | | 11 | | |
| | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | | |
| Static | | | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | $V_{GS} = 0V, I_D = 250\mu A$ | 600 | | | V | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 600V, V_{GS} = 0V, T_{J} = 25^{\circ}C$ | | | 1 | μA | | |
| Gate-Source Leakage | I _{GSS} | V_{GS} = $\pm 30V$ | | | ±100 | nA | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 3.0 | | 4.0 | V | | |
| Drain-Source On-Resistance (Note3) | R _{DS(on)} | $V_{GS} = 10V, I_{D} = 10A$ | | 0.43 | 0.50 | Ω | | |
| Dynamic | | | | | | | | |
| Input Capacitance | C _{iss} | V _{GS} = 0V, | | 2718 | | pF | | |
| Output Capacitance | C _{oss} | $V_{DS} = 25V,$ | | 242 | | | | |
| Reverse Transfer Capacitance | C _{rss} | f = 1.0MHz | | 24 | | | | |
| Total Gate Charge | Qg | | | 75 | | nC | | |
| Gate-Source Charge | Q _{gs} | $V_{DD} = 480V, I_{D} = 20A, V_{GS} = 10V$ | | 12 | | | | |
| Gate-Drain Charge | Q_{gd} | | | 34 | | | | |
| Turn-on Delay Time | t _{d(on)} | | | 54 | | ns | | |
| Turn-on Rise Time | t _r | V _{DD} = 250V, I _D = 20A, | | 30 | | | | |
| Turn-off Delay Time | t _{d(off)} | $R_{\rm G} = 25 \Omega$ | | 313 | | | | |
| Turn-off Fall Time | t _f | | | 59 | | | | |
| Drain-Source Body Diode Character | istics | | | | | | | |
| Continuous Body Diode Current | ۱ _s | | | | 20 | A | | |
| Pulsed Diode Forward Current | I _{SM} | T _C = 25 °C | | | 80 | | | |
| Body Diode Voltage | V _{SD} | $T_J = 25^{\circ}C, I_{SD} = 10A, V_{GS} = 0V$ | | | 1.4 | V | | |
| Reverse Recovery Time | t _{rr} | V _{GS} = 0V,I _S = 20A, | | 154 | | ns | | |
| Reverse Recovery Charge | Q _{rr} | di _F /dt =100A /µs | | 0.42 | | μC | | |

Notes

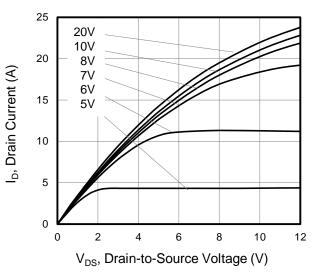
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%

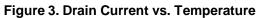


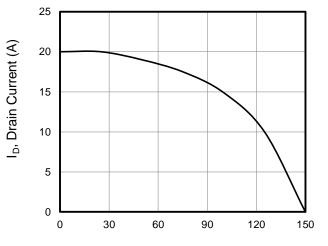
Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

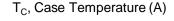
Figure 1. Output Characteristics ($T_J = 25^{\circ}C$)

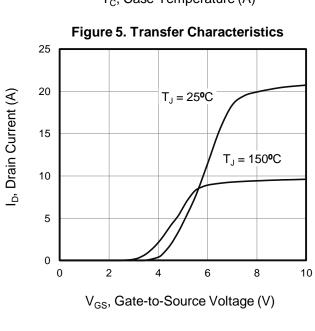
Figure 2. Body Diode Forward Voltage

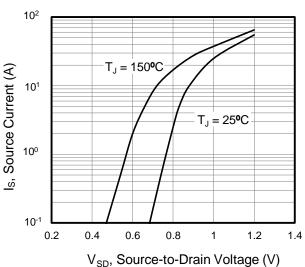














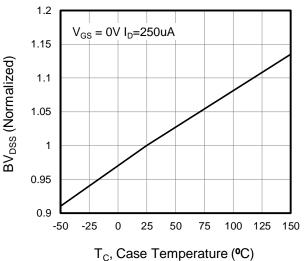
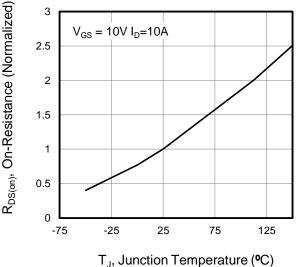


Figure 6. On-Resistance vs. Temperature





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

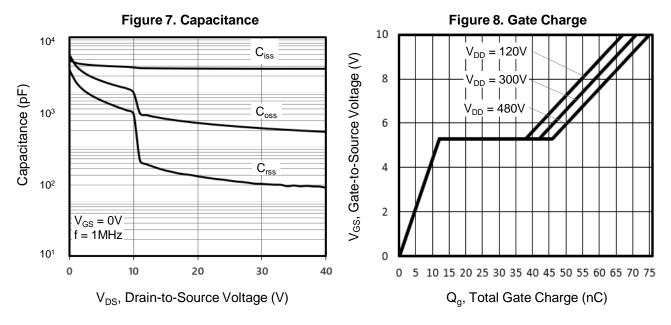
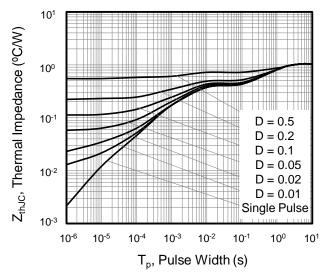


Figure 9. Transient Thermal Impedance

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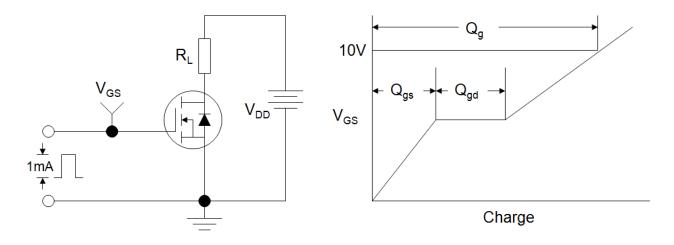


Figure B: Resistive Switching Test Circuit and Waveform

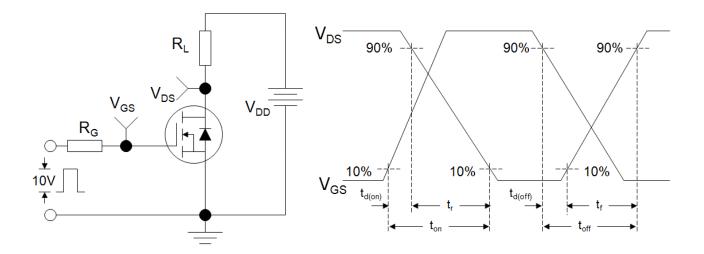
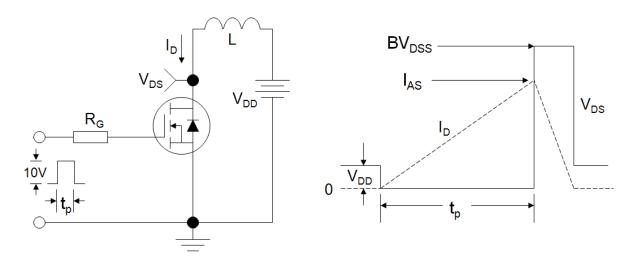


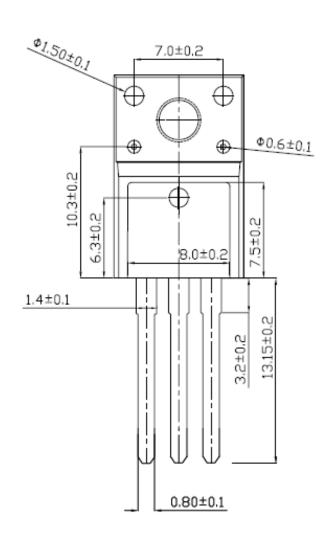
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

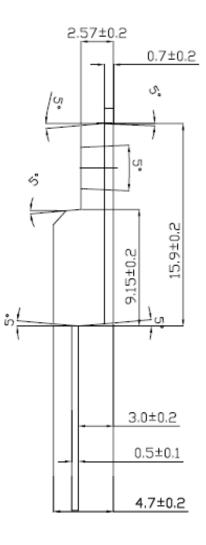






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